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(54) **SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

A semiconductor device includes a gate line extending in a first direction, parallel to an upper surface of a semiconductor substrate; a first active region including a first channel region disposed below the gate line and including a first conductivity-type impurity; a second active region disposed to be separated from the first active region in the first direction, including a second channel region disposed below the gate line, and including the first conductivity-type impurity; and a plurality of metal wirings disposed at a first height level above the semiconductor substrate, wherein at least one metal wiring, among the plurality of metal wirings, is directly electrically connected to the first active region, no metal wirings at the first height level are electrically connected to the second active region, and at least one metal wiring, among the plurality of metal wirings, is connected to receive a signal applied to the gate line.

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